1 Product profile

1.1 General description

NPN general-purpose transistors in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package.

Table 1. Product overview

Type number	number Package Nexperia JEDEC		PNP complement
BC817K-16H	SOT23	TO-236AB	-
BC817K-25H			-
BC817K-40H			-

1.2 Features and benefits

- · Three current gain selections
- · High power dissipation capability
- High-temperature applications up to 175 °C
- AEC-Q101 qualified

1.3 Applications

General-purpose switching and amplification

1.4 Quick reference data

Table 2. Quick reference data

 T_{amb} = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{CEO}	collector-emitter voltage	open base		-	-	45	V
I _C	collector current			-	-	500	mA
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	-	1	Α
h _{FE}	DC current gain	V _{CE} = 1 V; I _C = 100 mA					
	BC817K-16H		[1]	100	-	250	-
	BC817K-25H		[1]	160	-	400	-
	BC817K-40H		[1]	250	-	600	-

[1] pulsed; tp \leq 300 μ s; $\delta \leq$ 0.02



2 Pinning information

Table 3. Pinning

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base		
2	E	emitter] 3	С
3	С	collector	1 2	BE sym123

3 Ordering information

Table 4. Ordering information

Type number	Package	Package					
	Name	Description	Version				
BC817K-16H	TO-236AB	Plastic surface-mounted package; 3 leads	SOT23				
BC817K-25H							
BC817K-40H							

4 Marking

Table 5. Marking

Tuble 6. Marking		
Type number		Marking code
BC817K-16H		%HD
BC817K-25H		%HE
BC817K-40H	[1]	%HF

[1] % = placeholder for manufacturing site code

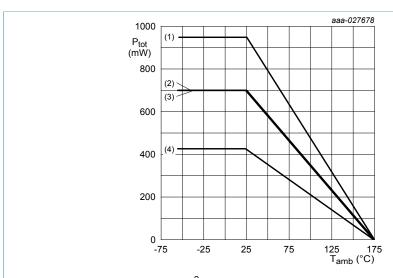
Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter		-	50	V
V _{CEO}	collector-emitter voltage	open base		-	45	V
V_{EBO}	emitter-base voltage	open collector		-	7	V
I _C	collector current			-	500	mA
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	1	Α
I _{BM}	peak base current	single pulse; t _p ≤ 1 ms		-	200	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	425	mW
			[2]	-	700	mW
			[3]	-	700	mW
			[4]	-	950	mW
Tj	junction temperature			-	175	°C
T _{amb}	ambient temperature			-55	175	°C
T _{stg}	storage temperature			-65	175	°C

- Device mounted on an FR4 Printed-Circuit-Board (PCB); single-sided copper; tin-plated and standard footprint.
- Device mounted on an FR4 Printed-Circuit-Board (PCB); single-sided copper; tin-plated; mounting pad for collector 1 cm². Device mounted on an FR4 Printed-Circuit-Board (PCB); 4-layer copper; tin-plated and standard footprint. Device mounted on an FR4 Printed-Circuit-Board (PCB); 4-layer copper; tin-plated; mounting pad for collector 1 cm².

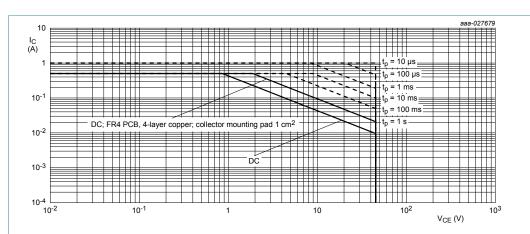


- (1) FR4 PCB, 4-layer copper; 1 cm²
- (2) FR4 PCB, single-sided copper; 1 cm²
- (3) FR4 PCB, 4-layer copper; standard footprint
- (4) FR4 PCB, single-sided copper; standard footprint

Figure 1. Power derating curves

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FR4 PCB, single-sided copper; standard footprint; single pulse

 T_{amb} = 25 °C

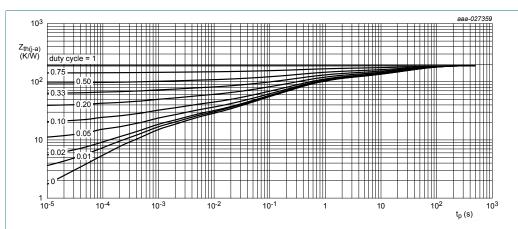
Figure 2. Safe operating area; junction to ambient; continous and peak collector currents as a function of collector-emitter voltage

Thermal characteristics

Table 7. Thermal characteristics

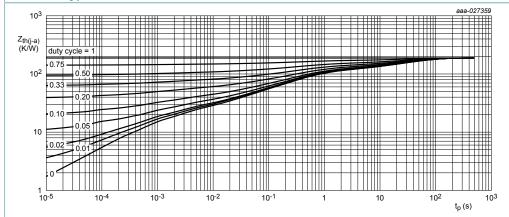
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from junction	in free air	[1]	-	-	353	K/W
	to ambient		[2]	-	-	215	K/W
		[3]	[3]	-	-	215	K/W
			[4]	-	-	158	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	-	60	K/W

- Device mounted on an FR4 PCB; single-sided copper; tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB; single-sided copper; tin-plated; mounting pad for collector 1 cm².
- Device mounted on an FR4 PCB; 4-layer copper; tin-plated and standard footprint.
- [3] [4] Device mounted on an FR4 PCB; 4-layer copper; tin-plated; mounting pad for collector 1 cm².



FR4 PCB; single-sided copper; tin-plated and standard footprint

Figure 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



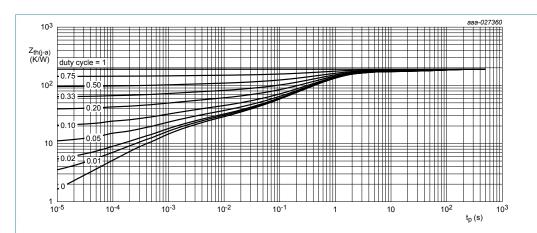
FR4 PCB; single-sided copper; tin-plated; mounting pad for collector 1 cm²

Figure 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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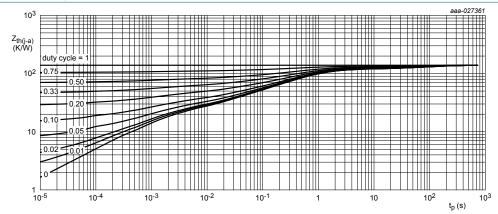
Product data sheet

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FR4 PCB; 4-layer copper; tin plated and standard footprint

Figure 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB; 4-layer copper; tin plated; mounting pad for collector 1 cm²

Figure 6. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

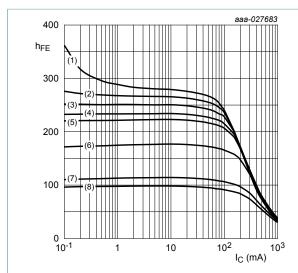
7 Characteristics

Table 8. Characteristics

 T_{amb} = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{(BR)CBO}	collector-base breakdown voltage	$I_C = 100 \mu A; I_E = 0 A$		50	-	-	V
$V_{(BR)CEO}$	collector-emitter breakdown voltage	I _C = 10 mA; I _B = 0 A		45	-	-	V
$V_{(BR)EBO}$	emitter-base breakdown voltage	$I_E = 100 \ \mu A; I_C = 0 \ A$		7	-	-	V
I _{CBO}	collector-base	V _{CB} = 25 V; I _E = 0 A		-	-	100	nA
	cut-off current	V _{CB} = 25 V; I _E = 0 A; T _j = 150 °C		-	-	5	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}$		-	-	100	nA
h _{FE}	DC current gain			· ·	'		
	BC817K-16H	V _{CE} = 1 V; I _C = 100 mA	[1]	100	-	250	
	BC817K-25H	V _{CE} = 1 V; I _C = 100 mA	[1]	160	-	400	
	BC817K-40H	V _{CE} = 1 V; I _C = 100 mA	[1]	250	-	600	
	BC817K-16H, -25H, -40H	V _{CE} = 1 V; I _C = 500 mA	[1]	40	-	-	
V _{CEsat}	collector-emitter saturation voltage	$I_C = 500 \text{ mA}; I_B = 50 \text{ mA}$	[1]	-	-	700	mV
V _{BEsat}	base-emitter saturation voltage	$I_C = 500 \text{ mA}; I_B = 50 \text{ mA}$	[1]	-	-	1.2	V
V _{BE}	base-emitter voltage	V _{CE} = 1 V; I _C = 500 mA	[1]	-	-	1.2	V
f _T	transition frequency	$V_{CE} = 5 \text{ V}; I_{C} = 10 \text{ mA}; f = 100 \text{ MHz}$		100	-	-	MHz
C _c	collector capacitance	V _{CB} = 10 V; I _E = i _e = 0 A; f = 1 MHz		-	3	-	pF
C _e	emitter capacitance	$V_{EB} = 0.5 \text{ V}; I_C = I_c = 0 \text{ A}; f = 1 \text{ MHz}$					
	BC817K-16H			-	44	-	pF
	BC817K-25H			-	39	-	pF
	BC817K-40H			-	39	-	pF

^[1] pulsed; $t_p \le 300 \ \mu s$; $\delta \le 0.02$



 $V_{CE} = 1 V$

(1) $T_{amb} = 175$ °C

(2) T_{amb} = 150 °C

(3) T_{amb} = 125 °C

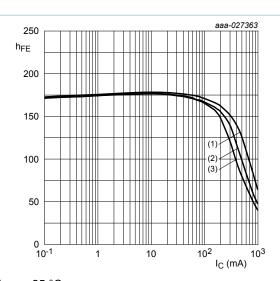
(4) T_{amb} = 100 °C

(5) $T_{amb} = 85 \, ^{\circ}C$

(6) T_{amb} = 25 °C

(7) $T_{amb} = -40 \, ^{\circ}C$ (8) $T_{amb} = -55 \, ^{\circ}C$

Figure 7. BC817K-16H: DC current gain as a function of collector current; typical values



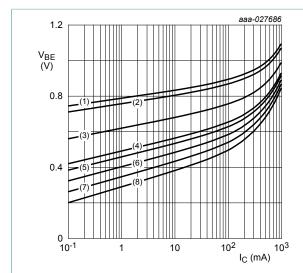
 T_{amb} = 25 °C

(1) $V_{CE} = 5 V$

(2) V_{CE} = 2 V

(3) $V_{CE} = 1 V$

Figure 8. BC817K-16H: DC current gain as a function of collector current; typical values



 $V_{CE} = 1 V$

(1)
$$T_{amb} = -55$$
 °C

(2)
$$T_{amb} = -40^{\circ}C$$

(3)
$$T_{amb}$$
 = 25 °C

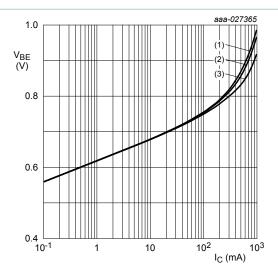
(4)
$$T_{amb}$$
 = 85 °C

(5)
$$T_{amb}$$
 = 100 °C

$$(7) T_{amb} = 150 °C$$

(8)
$$T_{amb} = 175 \, ^{\circ}C$$

Figure 9. BC817K-16H: Base-emitter voltage as a function of collector current; typical values



T_{amb} = 25 °C

(1)
$$V_{CE} = 1 V$$

(2)
$$V_{CE} = 2 V$$

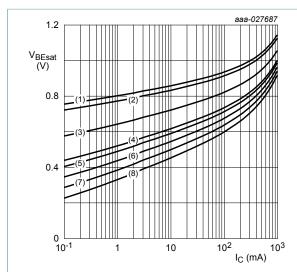
(3)
$$V_{CE} = 5 V$$

Figure 10. BC817K-16H: Base-emitter voltage as a function of collector current; typical values

10²

10³

I_C (mA)



 $I_C/I_B = 10$

(1)
$$T_{amb} = -55$$
 °C

(2)
$$T_{amb} = -40^{\circ}C$$

(3)
$$T_{amb} = 25 \, ^{\circ}C$$

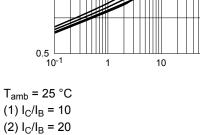
(4)
$$T_{amb} = 85 \, ^{\circ}C$$

(5)
$$T_{amb} = 100 \, ^{\circ}C$$

(6)
$$T_{amb} = 125 ^{\circ}C$$

$$(7) T_{amb} = 150 °C$$

(8)
$$T_{amb} = 175 \, ^{\circ}C$$



(2)
$$I_C/I_B = 20$$

1.1

0.9

0.7

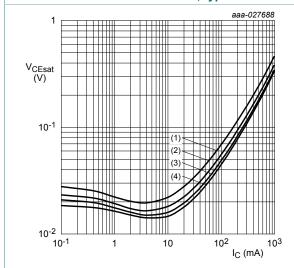
V_{BEsat} (V)

(3)
$$I_C/I_B = 50$$

$$(4) I_C/I_B = 100$$

Figure 12. BC817K-16H: Base-emitter saturation voltage as a function of collector current; typical values





 $I_{\rm C}/I_{\rm B}=10$

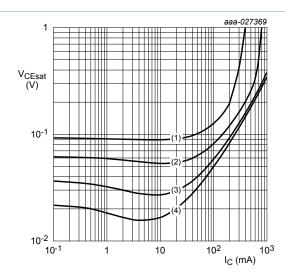
(1)
$$T_{amb} = 175 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 85 °C

(3)
$$T_{amb} = 25 \, ^{\circ}C$$

(4)
$$T_{amb}$$
 = -40 °C

Figure 13. BC817K-16H: Collector-emitter saturation voltage as a function of collector current; typical values



T_{amb} = 25 °C

(1)
$$I_C/I_B = 100$$

(2)
$$I_C/I_B = 50$$

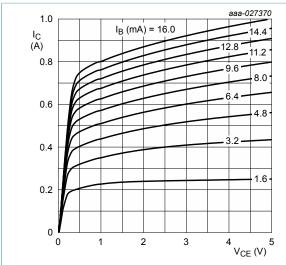
(3)
$$I_C/I_B = 20$$

$$(4) I_C/I_B = 10$$

Figure 14. BC817K-16H: Collector-emitter saturation voltage as a function of collector current; typical values

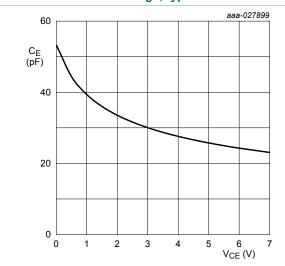
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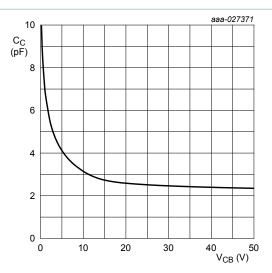
 $T_{amb} = 25 \, ^{\circ}C$

Figure 15. BC817K-16H: Collector current as a function of collector-emitter voltage; typical values



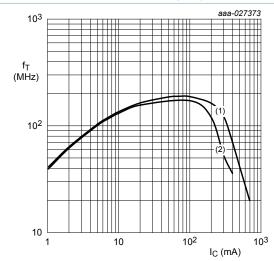
 $f = 1 \text{ MHz}; T_{amb} = 25 \text{ }^{\circ}\text{C}$

Figure 17. BC817K-16H: Emitter capacitance as a function of emitter-base voltage; typical values



f = 1 MHz; T_{amb} = 25 °C

Figure 16. BC817K-16H: Collector capacitance as a function of collector-base voltage; typical values

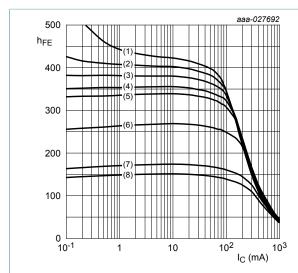


 $f = 100 \text{ MHz}; T_{amb} = 25 \text{ }^{\circ}\text{C}$

(1) $V_{CE} = 5 V$

(2) $V_{CE} = 1 V$

Figure 18. BC817K-16H: Transition frequency as a function of collector current voltage; typical values



 $V_{CE} = 1 V$

(1) $T_{amb} = 175$ °C

(2) T_{amb} = 150 °C

(3) T_{amb} = 125 °C

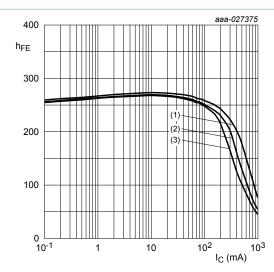
(4) T_{amb} = 100 °C

(5) T_{amb} = 85 °C

(6) T_{amb} = 25 °C

(7) $T_{amb} = -40 \, ^{\circ}C$ (8) $T_{amb} = -55 \, ^{\circ}C$

Figure 19. BC817K-25H: DC current gain as a function of collector current; typical values



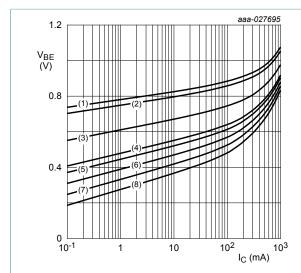
 $T_{amb} = 25 \, ^{\circ}C$

(1) $V_{CE} = 5 V$

(2) $V_{CE} = 2 V$

(3) $V_{CE} = 1 V$

Figure 20. BC817K-25H: DC current gain as a function of collector current; typical values



 $V_{CE} = 1 V$

(1) $T_{amb} = -55$ °C

(2) $T_{amb} = -40^{\circ}C$

(3) T_{amb} = 25 °C

(4) T_{amb} = 85 °C

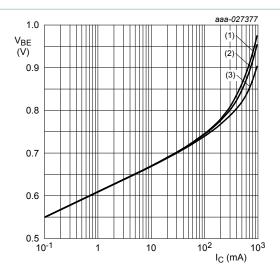
(5) $T_{amb} = 100 \, ^{\circ}C$

(6) T_{amb} = 125 °C

 $(7) T_{amb} = 150 °C$

(8) T_{amb} = 175 °C

Figure 21. BC817K-25H: Base-emitter voltage as a function of collector current; typical values



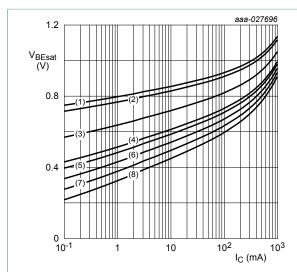
T_{amb} = 25 °C

(1) $V_{CE} = 1 V$

(2) $V_{CE} = 2 V$

(3) $V_{CE} = 5 V$

Figure 22. BC817K-25H: Base-emitter voltage as a function of collector current; typical values



 $I_{\rm C}/I_{\rm B}=10$

(1)
$$T_{amb} = -55$$
 °C

(2)
$$T_{amb} = -40^{\circ}C$$

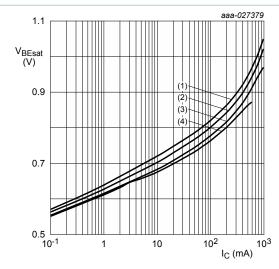
$$(3) T_{amb} = 25 °C$$

(5)
$$T_{amb} = 100 \, ^{\circ}C$$

(6)
$$T_{amb} = 125 \, ^{\circ}C$$

$$(7) T_{amb} = 150 °C$$

(8)
$$T_{amb} = 175 \, ^{\circ}C$$



T_{amb} = 25 °C

(1)
$$I_C/I_B = 10$$

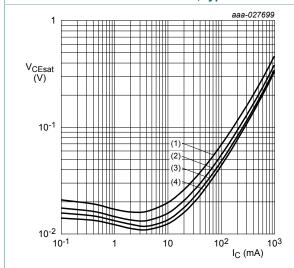
(2)
$$I_C/I_B = 20$$

(3)
$$I_C/I_B = 50$$

$$(4) I_C/I_B = 100$$

Figure 24. BC817K-25H: Base-emitter saturation voltage as a function of collector current; typical values





 $I_{\rm C}/I_{\rm B}=10$

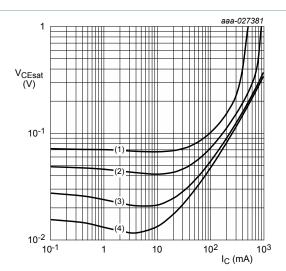
(1)
$$T_{amb} = 175 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 85 °C

(3)
$$T_{amb} = 25 \, ^{\circ}C$$

(4)
$$T_{amb}$$
 = -40 °C

Figure 25. BC817K-25H: Collector-emitter saturation voltage as a function of collector current; typical values



T_{amb} = 25 °C

(1)
$$I_C/I_B = 100$$

(2)
$$I_C/I_B = 50$$

(3)
$$I_C/I_B = 20$$

$$(4) I_C/I_B = 10$$

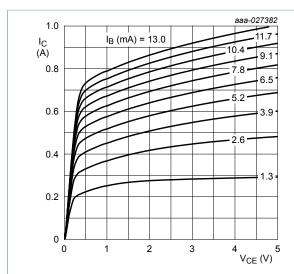
Figure 26. BC817K-25H: Collector-emitter saturation voltage as a function of collector current; typical values

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45 V, 500 mA NPN general-purpose transistors



 $T_{amb} = 25 \, ^{\circ}C$

Figure 27. BC817K-25H: Collector current as a function of collector-emitter voltage; typical values

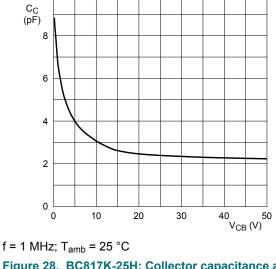
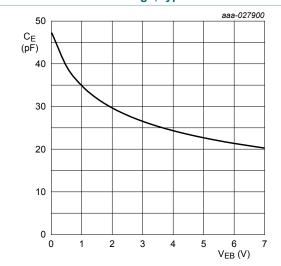
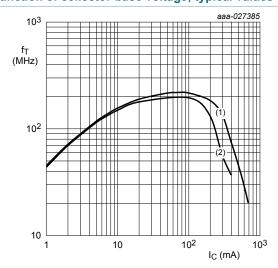


Figure 28. BC817K-25H: Collector capacitance as a function of collector-base voltage; typical values



 $f = 1 \text{ MHz}; T_{amb} = 25 \text{ }^{\circ}\text{C}$

Figure 29. BC817K-25H: Emitter capacitance as a function of emitter-base voltage; typical values



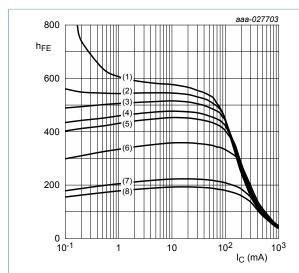
 $f = 100 \text{ MHz}; T_{amb} = 25 \text{ }^{\circ}\text{C}$

(1) $V_{CE} = 5 V$

10

(2) $V_{CE} = 1 V$

Figure 30. BC817K-25H: Transition frequency as a function of collector current voltage; typical values



 $V_{CE} = 1 V$

(1) $T_{amb} = 175$ °C

(2) T_{amb} = 150 °C

(3) T_{amb} = 125 °C

(4) T_{amb} = 100 °C

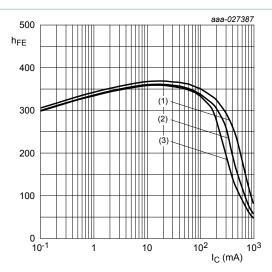
(5) $T_{amb} = 85 \, ^{\circ}C$

(6) T_{amb} = 25 °C

(7) T_{amb} = -40 °C

(8) T_{amb} = -55 °C

Figure 31. BC817K-40H: DC current gain as a function of collector current; typical values



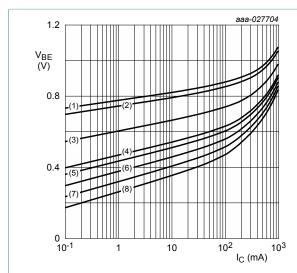
T_{amb} = 25 °C

(1) $V_{CE} = 5 V$

(2) V_{CE} = 2 V

(3) $V_{CE} = 1 V$

Figure 32. BC817K-40H: DC current gain as a function of collector current; typical values



 $V_{CE} = 1 V$

(1) $T_{amb} = -55$ °C

(2) $T_{amb} = -40^{\circ}C$

(3) T_{amb} = 25 °C

(4) T_{amb} = 85 °C

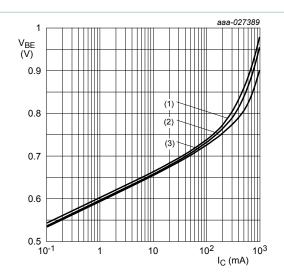
(5) $T_{amb} = 100 \, ^{\circ}C$

(6) T_{amb} = 125 °C

 $(7) T_{amb} = 150 °C$

(8) $T_{amb} = 175 \, ^{\circ}C$

Figure 33. BC817K-40H: Base-emitter voltage as a function of collector current; typical values



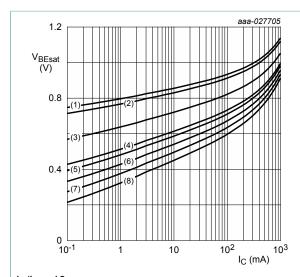
T_{amb} = 25 °C

(1) $V_{CE} = 1 V$

(2) $V_{CE} = 2 V$

(3) $V_{CE} = 5 V$

Figure 34. BC817K-40H: Base-emitter voltage as a function of collector current; typical values



 $I_{\rm C}/I_{\rm B}=10$

(1) $T_{amb} = -55$ °C

(2) $T_{amb} = -40^{\circ}C$

(3) $T_{amb} = 25 \, ^{\circ}C$

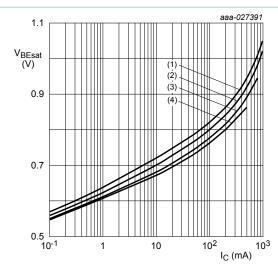
(4) $T_{amb} = 85 \, ^{\circ}C$

(5) $T_{amb} = 100 \, ^{\circ}C$

(6) T_{amb} = 125 °C

 $(7) T_{amb} = 150 °C$

(8) $T_{amb} = 175 \, ^{\circ}C$



T_{amb} = 25 °C

(1) $I_C/I_B = 10$

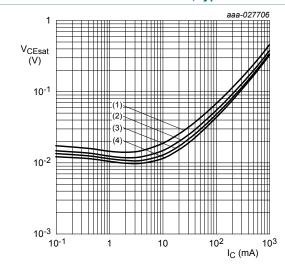
(2) $I_C/I_B = 20$

(3) $I_C/I_B = 50$

 $(4) I_C/I_B = 100$

Figure 36. BC817K-40H: Base-emitter saturation voltage as a function of collector current; typical values





 $I_{\rm C}/I_{\rm B}=10$

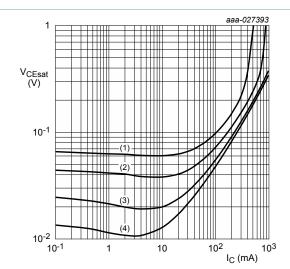
(1) $T_{amb} = 175 \, ^{\circ}C$

(2) T_{amb} = 85 °C

(3) $T_{amb} = 25 \, ^{\circ}C$

(4) T_{amb} = -40 °C

Figure 37. BC817K-40H: Collector-emitter saturation voltage as a function of collector current; typical values



 T_{amb} = 25 °C

(1) $I_C/I_B = 100$

(2) $I_C/I_B = 50$

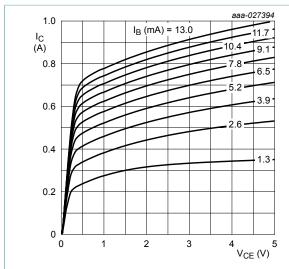
(3) $I_C/I_B = 20$

 $(4) I_C/I_B = 10$

Figure 38. BC817K-40H: Collector-emitter saturation voltage as a function of collector current; typical values

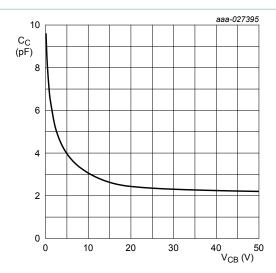
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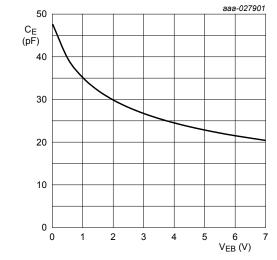
 $T_{amb} = 25 \, ^{\circ}C$

Figure 39. BC817K-40H: Collector current as a function of collector-emitter voltage; typical values



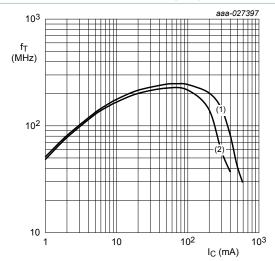
f = 1 MHz; T_{amb} = 25 °C

Figure 40. BC817K-40H: Collector capacitance as a function of collector-base voltage; typical values



f = 1 MHz; $T_{amb} = 25 \text{ °C}$

Figure 41. BC817K-40H: Emitter capacitance as a function of emitter-base voltage; typical values



f = 100 MHz; $T_{amb} = 25 \,^{\circ}\text{C}$

(1) $V_{CE} = 5 V$

(2) $V_{CE} = 1 V$

Figure 42. BC817K-40H: Transition frequency as a function of collector current voltage; typical values

8 Test information

8.1 Quality information

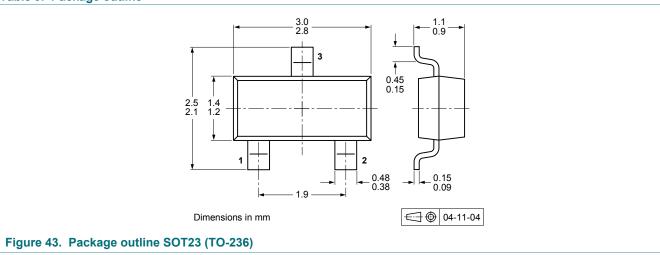
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

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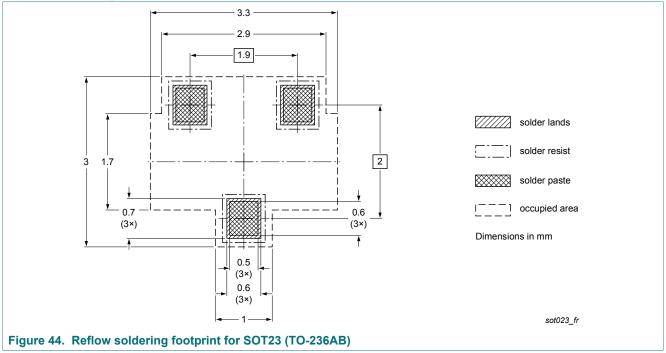
9 Package outline

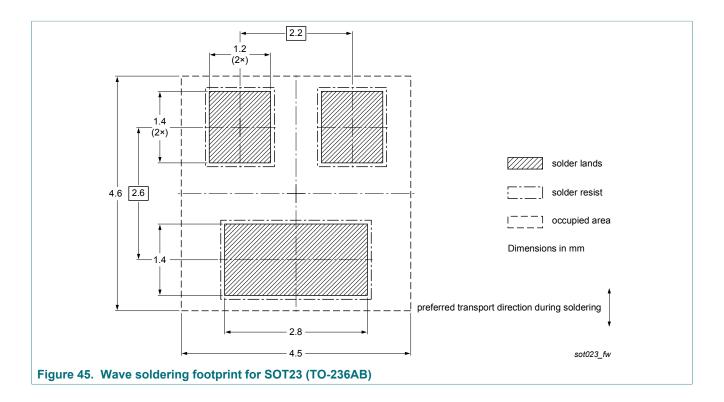
Table 9. Package outline



10 Soldering

Table 10. Soldering





BC817KH series

45 V, 500 mA NPN general-purpose transistors

11 Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BC817KH_SER v.1	20171215	Product data sheet	-	-

12 Legal information

12.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- The term 'short data sheet' is explained in section "Definitions". [2] [3]
- The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nexperia.com.

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